High Voltage Latch-Up Proof, 4-/8-Channel Multiplexers

Enhanced Product

ADG5408-EP/ADG5409-EP

FEATURES

- Latch-up proof
- 8 kV human body model (HBM) ESD rating
- Low on resistance (13.5 Ω)
- ±9 V to ±22 V dual-supply operation
- 9 V to 40 V single-supply operation
- Fully specified at ±15 V, ±20 V, +12 V, and +36 V
- V_{SS} to V_{DD} analog signal range

ENHANCED PRODUCT FEATURES

- Supports defense and aerospace applications (AQEC standard)
- Military temperature range: −55°C to +125°C
- Controlled manufacturing baseline
- One assembly/test site
- One fabrication site
- Enhanced product change notification
- Qualification data available on request

APPLICATIONS

- Relay replacement
- Automatic test equipment
- Data acquisition
- Instrumentation
- Avionics
- Communication systems

FUNCTIONAL BLOCK DIAGRAMS

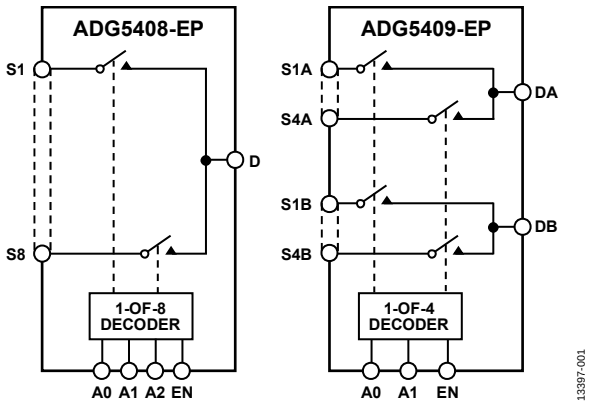

Figure 1.

GENERAL DESCRIPTION

The ADG5408-EP/ADG5409-EP are monolithic CMOS analog multiplexers comprising eight single channels and four differential channels, respectively. The ADG5408-EP switches one of eight inputs to a common output, as determined by the 3-bit binary address lines, A0, A1, and A2. The ADG5409-EP switches one of four differential inputs to a common differential output, as determined by the 2-bit binary address lines, A0 and A1.

An EN input on both devices enables or disables the device. When EN is disabled, all channels switch off. The on-resistance profile is very flat over the full analog input range, which ensures good linearity and low distortion when switching audio signals. High switching speed also makes the parts suitable for video signal switching.

Each switch conducts equally well in both directions when on, and each switch has an input signal range that extends to the power supplies. In the off condition, signal levels up to the supplies are blocked.

The ADG5408-EP/ADG5409-EP do not have V_L pins; rather, the logic power supply is generated internally by an on-chip voltage generator.

Additional application and technical information can be found in the ADG5408/ADG5409 data sheet.

PRODUCT HIGHLIGHTS

1. Trench isolation guards against latch-up. A dielectric trench separates the P and N channel transistors thereby preventing latch-up even under severe overvoltage conditions.
2. Low R_{ON}.
3. Dual-supply operation. For applications where the analog signal is bipolar, the ADG5408-EP/ADG5409-EP can be operated from dual supplies up to ±22 V.
4. Single-supply operation. For applications where the analog signal is unipolar, the ADG5408-EP/ADG5409-EP can be operated from a single rail power supply up to 40 V.
5. 3 V logic compatible digital inputs: V_{INH} = 2.0 V, V_{INL} = 0.8 V.
6. No V_L logic power supply required.

Rev. 0 Document Feedback

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REVISION HISTORY

9/15—Revision 0: Initial Version

SPECIFICATIONS

±15 V DUAL SUPPLY

V_{DD} = +15 V ± 10%, V_{SS} = −15 V ± 10%, GND = 0 V, unless otherwise noted.

Table 1.

Parameter	25°C	−40°C to +85°C	−55°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			V_{DD} to V_{SS}	V	
On Resistance, R_{ON}	13.5			Ω typ	V_S = ±10 V, I_S = −10 mA; see Figure 24
	15	18	22	Ω max	V_{DD} = +13.5 V, V_{SS} = −13.5 V
On-Resistance Match Between Channels, ΔR_{ON}	0.3			Ω typ	V_S = ±10 V, I_S = −10 mA
	0.8	1.3	1.4	Ω max	
On-Resistance Flatness, $R_{FLAT (ON)}$	1.8			Ω typ	V_S = ±10 V, I_S = −10 mA
	2.2	2.6	3	Ω max	
LEAKAGE CURRENTS					V_{DD} = +16.5 V, V_{SS} = −16.5 V
Source Off Leakage, I_S (Off)	±0.05			nA typ	V_S = ±10 V, V_D = ∓10 V; see Figure 27
	±0.25	±1	±7	nA max	
Drain Off Leakage, I_D (Off)	±0.1			nA typ	V_S = ±10 V, V_D = ∓10 V; see Figure 27
	±0.4	±4	±30	nA max	
Channel On Leakage, I_D (On), I_S (On)	±0.1			nA typ	V_S = V_D = ±10 V; see Figure 23
	±0.4	±4	±30	nA max	
DIGITAL INPUTS					
Input High Voltage, V_{INH}			2.0	V min	
Input Low Voltage, V_{INL}			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.002			μA typ	V_{IN} = V_{GND} or V_{DD}
			±0.1	μA max	
Digital Input Capacitance, C_{IN}	3			pF typ	
DYNAMIC CHARACTERISTICS[1]					
Transition Time, $t_{TRANSITION}$	170			ns typ	R_L = 300 Ω, C_L = 35 pF
	217	258	292	ns max	V_S = 10 V; see Figure 30
t_{ON} (EN)	140			ns typ	R_L = 300 Ω, C_L = 35 pF
	175	213	242	ns max	V_S = 10 V; see Figure 32
t_{OFF} (EN)	130			ns typ	R_L = 300 Ω, C_L = 35 pF
	161	183	198	ns max	V_S = 10 V; see Figure 32
Break-Before-Make Time Delay, t_D	50			ns typ	R_L = 300 Ω, C_L = 35 pF
			13	ns min	V_{S1} = V_{S2} = 10 V; see Figure 31
Charge Injection, Q_{INJ}	115			pC typ	V_S = 0 V, R_S = 0 Ω, C_L = 1 nF; see Figure 33
Off Isolation	−60			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; see Figure 26
Channel-to-Channel Crosstalk	−60			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; see Figure 25
Total Harmonic Distortion + Noise	0.01			% typ	R_L = 1 kΩ, 15 V p-p, f = 20 Hz to 20 kHz; see Figure 28
−3 dB Bandwidth					R_L = 50 Ω, C_L = 5 pF; see Figure 29
ADG5408-EP	50			MHz typ	
ADG5409-EP	87			MHz typ	
Insertion Loss	0.9			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; Figure 29
C_S (Off)	15			pF typ	V_S = 0 V, f = 1 MHz
C_D (Off)					
ADG5408-EP	102			pF typ	V_S = 0 V, f = 1 MHz
ADG5409-EP	50			pF typ	V_S = 0 V, f = 1 MHz

Parameter	25°C	−40°C to +85°C	−55°C to +125°C	Unit	Test Conditions/Comments
C_D (On), C_S (On)					
ADG5408-EP	133			pF typ	V_S = 0 V, f = 1 MHz
ADG5409-EP	81			pF typ	V_S = 0 V, f = 1 MHz
POWER REQUIREMENTS					V_{DD} = +16.5 V, V_{SS} = −16.5 V
I_{DD}	45			µA typ	Digital inputs = 0 V or V_{DD}
	55		80	µA max	
I_{SS}	0.001			µA typ	Digital inputs = 0 V or V_{DD}
			1	µA max	
V_{DD}/V_{SS}			±9/±22	V min/V max	GND = 0 V

[1] Guaranteed by design; not subject to production test.

±20 V DUAL SUPPLY

V_{DD} = +20 V ± 10%, V_{SS} = −20 V ± 10%, GND = 0 V, unless otherwise noted.

Table 2.

Parameter	25°C	−40°C to +85°C	−55°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			V_{DD} to V_{SS}	V	
On Resistance, R_{ON}	12.5			Ω typ	V_S = ±15 V, I_S = −10 mA; see Figure 24
	14	17	21	Ω max	V_{DD} = +18 V, V_{SS} = −18 V
On-Resistance Match Between Channels, ΔR_{ON}	0.3			Ω typ	V_S = ±15 V, I_S = −10 mA
	0.8	1.3	1.4	Ω max	
On-Resistance Flatness, $R_{FLAT (ON)}$	2.3			Ω typ	V_S = ±15 V, I_S = −10 mA
	2.7	3.1	3.5	Ω max	
LEAKAGE CURRENTS					V_{DD} = +22 V, V_{SS} = −22 V
Source Off Leakage, I_S (Off)	±0.1			nA typ	V_S = ±15 V, V_D = ∓15 V; see Figure 27
	±0.25	±1	±7	nA max	
Drain Off Leakage, I_D (Off)	±0.15			nA typ	V_S = ±15 V, V_D = ∓15 V; see Figure 27
	±0.4	±4	±30	nA max	
Channel On Leakage, I_D (On), I_S (On)	±0.15			nA typ	V_S = V_D = ±15 V; see Figure 23
	±0.4	±4	±30	nA max	
DIGITAL INPUTS					
Input High Voltage, V_{INH}			2.0	V min	
Input Low Voltage, V_{INL}			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.002			µA typ	V_{IN} = V_{GND} or V_{DD}
			±0.1	µA max	
Digital Input Capacitance, C_{IN}	3			pF typ	
DYNAMIC CHARACTERISTICS[1]					
Transition Time, $t_{TRANSITION}$	160			ns typ	R_L = 300 Ω, C_L = 35 pF
	207	237	262	ns max	V_S = 10 V; see Figure 30
t_{ON} (EN)	140			ns typ	R_L = 300 Ω, C_L = 35 pF
	165	194	218	ns max	V_S = 10 V; see Figure 32
t_{OFF} (EN)	133			ns typ	R_L = 300 Ω, C_L = 35 pF
	153	174	189	ns max	V_S = 10 V; see Figure 32
Break-Before-Make Time Delay, t_D	38			ns typ	R_L = 300 Ω, C_L = 35 pF
			8	ns min	V_{S1} = V_{S2} = 10 V; see Figure 31
Charge Injection, Q_{INJ}	155			pC typ	V_S = 0 V, R_S = 0 Ω, C_L = 1 nF; see Figure 33
Off Isolation	−60			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; see Figure 26
Channel-to-Channel Crosstalk	−60			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; see Figure 25

Parameter	25°C	−40°C to +85°C	−55°C to +125°C	Unit	Test Conditions/Comments
Total Harmonic Distortion + Noise	0.012			% typ	R_L = 1 kΩ, 20 V p-p, f = 20 Hz to 20 kHz; see Figure 28
−3 dB Bandwidth					R_L = 50 Ω, C_L = 5 pF; see Figure 29
ADG5408-EP	50			MHz typ	
ADG5409-EP	88			MHz typ	
Insertion Loss	0.8			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; see Figure 29
C_S (Off)	17			pF typ	V_S = 0 V, f = 1 MHz
C_D (Off)					
ADG5408-EP	98			pF typ	V_S = 0 V, f = 1 MHz
ADG5409-EP	48			pF typ	V_S = 0 V, f = 1 MHz
C_D (On), C_S (On)					
ADG5408-EP	128			pF typ	V_S = 0 V, f = 1 MHz
ADG5409-EP	80			pF typ	V_S = 0 V, f = 1 MHz
POWER REQUIREMENTS					V_{DD} = +22 V, V_{SS} = −22 V
I_{DD}	50			µA typ	Digital inputs = 0 V or V_{DD}
	70		120	µA max	
I_{SS}	0.001			µA typ	Digital inputs = 0 V or V_{DD}
			1	µA max	
V_{DD}/V_{SS}			±9/±22	V min/V max	GND = 0 V

[1] Guaranteed by design; not subject to production test.

12 V SINGLE SUPPLY

V_{DD} = 12 V ± 10%, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 3.

Parameter	25°C	−40°C to +85°C	−55°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 V to V_{DD}	V	
On Resistance, R_{ON}	26			Ω typ	V_S = 0 V to 10 V, I_S = −10 mA; see Figure 24
	30	36	42	Ω max	V_{DD} = 10.8 V, V_{SS} = 0 V
On-Resistance Match Between Channels, ΔR_{ON}	0.3			Ω typ	V_S = 0 V to 10 V, I_S = −10 mA
	1	1.5	1.6	Ω max	
On-Resistance Flatness, $R_{FLAT (ON)}$	5.5			Ω typ	V_S = 0 V to 10 V, I_S = −10 mA
	6.5	8	12	Ω max	
LEAKAGE CURRENTS					V_{DD} = 13.2 V, V_{SS} = 0 V
Source Off Leakage, I_S (Off)	±0.02			nA typ	V_S = 1 V/10 V, V_D = 10 V/1 V; see Figure 27
	±0.25	±1	±7	nA max	
Drain Off Leakage, I_D (Off)	±0.05			nA typ	V_S = 1 V/10 V, V_D = 10 V/1 V; see Figure 27
	±0.4	±4	±30	nA max	
Channel On Leakage, I_D (On), I_S (On)	±0.05			nA typ	V_S = V_D = 1 V/10 V; see Figure 23
	±0.4	±4	±30	nA max	
DIGITAL INPUTS					
Input High Voltage, V_{INH}			2.0	V min	
Input Low Voltage, V_{INL}			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.002			µA typ	V_{IN} = V_{GND} or V_{DD}
			±0.1	µA max	
Digital Input Capacitance, C_{IN}	3			pF typ	

Parameter	25°C	−40°C to +85°C	−55°C to +125°C	Unit	Test Conditions/Comments
DYNAMIC CHARACTERISTICS[1]					
Transition Time, $t_{TRANSITION}$	230			ns typ	R_L = 300 Ω, C_L = 35 pF
	321	388	430	ns max	V_S = 8 V; see Figure 30
t_{ON} (EN)	215			ns typ	R_L = 300 Ω, C_L = 35 pF
	276	345	397	ns max	V_S = 8 V; see Figure 32
t_{OFF} (EN)	134			ns typ	R_L = 300 Ω, C_L = 35 pF
	161	187	209	ns max	V_S = 8 V; see Figure 32
Break-Before-Make Time Delay, t_D	118			ns typ	R_L = 300 Ω, C_L = 35 pF
			44	ns min	V_{S1} = V_{S2} = 8 V; see Figure 31
Charge Injection, Q_{INJ}	45			pC typ	V_S = 6 V, R_S = 0 Ω, C_L = 1 nF; see Figure 33
Off Isolation	−60			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; see Figure 26
Channel-to-Channel Crosstalk	−60			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; see Figure 25
Total Harmonic Distortion + Noise	0.1			% typ	R_L = 1 kΩ, 6 V p-p, f = 20 Hz to 20 kHz; see Figure 28
−3 dB Bandwidth					R_L = 50 Ω, C_L = 5 pF; see Figure 29
ADG5408-EP	35			MHz typ	
ADG5409-EP	74			MHz typ	
Insertion Loss	−1.8			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; see Figure 29
C_S (Off)	22			pF typ	V_S = 6 V, f = 1 MHz
C_D (Off)					
ADG5408-EP	119			pF typ	V_S = 6 V, f = 1 MHz
ADG5409-EP	59			pF typ	V_S = 6 V, f = 1 MHz
C_D (On), C_S (On)					
ADG5408-EP	146			pF typ	V_S = 6 V, f = 1 MHz
ADG5409-EP	86			pF typ	V_S = 6 V, f = 1 MHz
POWER REQUIREMENTS					V_{DD} = 13.2 V
I_{DD}	40			µA typ	Digital inputs = 0 V or V_{DD}
	50		75	µA max	
V_{DD}			9/40	V min/V max	GND = 0 V, V_{SS} = 0 V

[1] Guaranteed by design; not subject to production test.

36 V SINGLE SUPPLY

V_{DD} = 36 V ± 10%, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 4.

Parameter	25°C	−40°C to +85°C	−55°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 V to V_{DD}	V	
On Resistance, R_{ON}	14.5			Ω typ	V_S = 0 V to 30 V, I_S = −10 mA; see Figure 24
	16	19	23	Ω max	V_{DD} = 32.4 V, V_{SS} = 0 V
On-Resistance Match Between Channels, ΔR_{ON}	0.3			Ω typ	V_S = 0 V to 30 V, I_S = −10 mA
	0.8	1.3	1.4	Ω max	
On-Resistance Flatness, $R_{FLAT (ON)}$	3.5			Ω typ	V_S = 0 V to 30 V, I_S = −10 mA
	4.3	5.5	6.5	Ω max	

Parameter	25°C	−40°C to +85°C	−55°C to +125°C	Unit	Test Conditions/Comments
LEAKAGE CURRENTS					V_{DD} =39.6 V, V_{SS} = 0 V
Source Off Leakage, I_S (Off)	±0.1			nA typ	V_S = 1 V/30 V, V_D = 30 V/1 V; see Figure 27
	±0.25	±1	±7	nA max	
Drain Off Leakage, I_D (Off)	±0.15			nA typ	V_S = 1 V/30 V, V_D = 30 V/1 V; see Figure 27
	±0.4	±4	±30	nA max	
Channel On Leakage, I_D (On), I_S (On)	±0.15			nA typ	V_S = V_D = 1 V/30 V; see Figure 23
	±0.4	±4	±30	nA max	
DIGITAL INPUTS					
Input High Voltage, V_{INH}			2.0	V min	
Input Low Voltage, V_{INL}			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.002			μA typ	V_{IN} = V_{GND} or V_{DD}
			±0.1	μA max	
Digital Input Capacitance, C_{IN}	3			pF typ	
DYNAMIC CHARACTERISTICS[1]					
Transition Time, $t_{TRANSITION}$	187			ns typ	R_L = 300 Ω, C_L = 35 pF
	242	257	281	ns max	V_S = 18 V; see Figure 30
t_{ON} (EN)	160			ns typ	R_L = 300 Ω, C_L = 35 pF
	195	219	237	ns max	V_S = 18 V; see Figure 32
t_{OFF} (EN)	147			ns typ	R_L = 300 Ω, C_L = 35 pF
	184	184	190	ns max	V_S = 18 V; see Figure 32
Break-Before-Make Time Delay, t_D	53			ns typ	R_L = 300 Ω, C_L = 35 pF
			14	ns min	V_{S1} = V_{S2} = 18 V; see Figure 31
Charge Injection, Q_{INJ}	150			pC typ	V_S = 18 V, R_S = 0 Ω, C_L = 1 nF; see Figure 33
Off Isolation	−60			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; see Figure 26
Channel-to-Channel Crosstalk	−60			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; see Figure 25
Total Harmonic Distortion + Noise	0.4			% typ	R_L = 1 kΩ, 18 V p-p, f = 20 Hz to 20 kHz; see Figure 28
−3 dB Bandwidth					R_L = 50 Ω, C_L = 5 pF; see Figure 29
ADG5408-EP	45			MHz typ	
ADG5409-EP	76			MHz typ	
Insertion Loss	−1			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; see Figure 29
C_S (Off)	18			pF typ	V_S = 18 V, f = 1 MHz
C_D (Off)					
ADG5408-EP	120			pF typ	V_S = 18 V, f = 1 MHz
ADG5409-EP	60			pF typ	V_S = 18 V, f = 1 MHz
C_D (On), C_S (On)					
ADG5408-EP	137			pF typ	V_S = 18 V, f = 1 MHz
ADG5409-EP	80			pF typ	V_S = 18 V, f = 1 MHz
POWER REQUIREMENTS					V_{DD} = 39.6 V
I_{DD}	80			μA typ	Digital inputs = 0 V or V_{DD}
	100		155	μA max	
V_{DD}			9/40	V min/V max	GND = 0 V, V_{SS} = 0 V

[1] Guaranteed by design; not subject to production test.

CONTINUOUS CURRENT PER CHANNEL, Sx OR D

Table 5. ADG5408-EP

Parameter	25°C	85°C	125°C	Unit
CONTINUOUS CURRENT, Sx OR D (θ_{JA} = 30.4°C/W)				
V_{DD} = +15 V, V_{SS} = −15 V	207	113	60	mA maximum
V_{DD} = +20 V, V_{SS} = −20 V	218	117	61	mA maximum
V_{DD} = 12 V, V_{SS} = 0 V	168	99	57	mA maximum
V_{DD} = 36 V, V_{SS} = 0 V	214	116	61	mA maximum

Table 6. ADG5409-EP

Parameter	25°C	85°C	125°C	Unit
CONTINUOUS CURRENT, Sx OR D (θ_{JA} = 30.4°C/W)				
V_{DD} = +15 V, V_{SS} = −15 V	156	95	55	mA maximum
V_{DD} = +20 V, V_{SS} = −20 V	165	98	56	mA maximum
V_{DD} = 12 V, V_{SS} = 0 V	126	81	50	mA maximum
V_{DD} = 36 V, V_{SS} = 0 V	161	97	56	mA maximum

ABSOLUTE MAXIMUM RATINGS

T_A = 25°C, unless otherwise noted.

Table 7.

Parameter	Rating
V_{DD} to V_{SS}	48 V
V_{DD} to GND	−0.3 V to +48 V
V_{SS} to GND	+0.3 V to −48 V
Analog Inputs[1]	V_{SS} − 0.3 V to V_{DD} + 0.3 V or 30 mA, whichever occurs first
Digital Inputs[1]	V_{SS} − 0.3 V to V_{DD} + 0.3 V or 30 mA, whichever occurs first
Peak Current, Sx or D Pins	
ADG5408-EP	435 mA (pulsed at 1 ms, 10% duty cycle maximum)
ADG5409-EP	300 mA (pulsed at 1 ms, 10% duty cycle maximum)
Continuous Current, Sx or D[2]	Data + 15%
Temperature Range	
Operating	−55°C to +125°C
Storage	−65°C to +150°C
Junction Temperature	150°C
Thermal Impedance, θ_{JA}	
16-Lead LFCSP (4-Layer Board)	30.4°C/W
Reflow Soldering Peak Temperature, Pb-Free	As per JEDEC J-STD-020

[1] Overvoltages at the Ax, EN, Sx, and D pins are clamped by internal diodes. Limit current to the maximum ratings given.
[2] See Table 5.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

Only one absolute maximum rating can be applied at any one time.

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

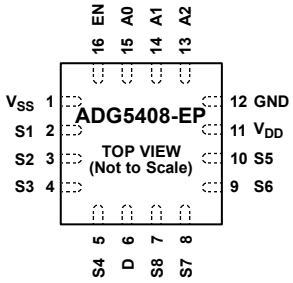

Figure 2. ADG5408-EP Pin Configuration

Table 8. ADG5408-EP Pin Function Descriptions

Pin No.	Mnemonic	Description
15	A0	Logic Control Input.
16	EN	Active High Digital Input. When low, the device is disabled and all switches are off. When high, Ax logic inputs determine on switches.
1	V_{SS}	Most Negative Power Supply Potential. In single-supply applications, this pin can be connected to ground.
2	S1	Source Terminal 1. This pin can be an input or an output.
3	S2	Source Terminal 2. This pin can be an input or an output.
4	S3	Source Terminal 3. This pin can be an input or an output.
5	S4	Source Terminal 4. This pin can be an input or an output.
6	D	Drain Terminal. This pin can be an input or an output.
7	S8	Source Terminal 8. This pin can be an input or an output.
8	S7	Source Terminal 7. This pin can be an input or an output.
9	S6	Source Terminal 6. This pin can be an input or an output.
10	S5	Source Terminal 5. This pin can be an input or an output.
11	V_{DD}	Most Positive Power Supply Potential.
12	GND	Ground (0 V) Reference.
13	A2	Logic Control Input.
14	A1	Logic Control Input.
EP	Exposed Pad	The exposed pad is connected internally. For increased reliability of the solder joints and maximum thermal capability, it is recommended that the pad be soldered to the substrate, V_{SS}.

Table 9. ADG5408-EP Truth Table

A2	A1	A0	EN	On Switch
X	X	X	0	None
0	0	0	1	1
0	0	1	1	2
0	1	0	1	3
0	1	1	1	4
1	0	0	1	5
1	0	1	1	6
1	1	0	1	7
1	1	1	1	8

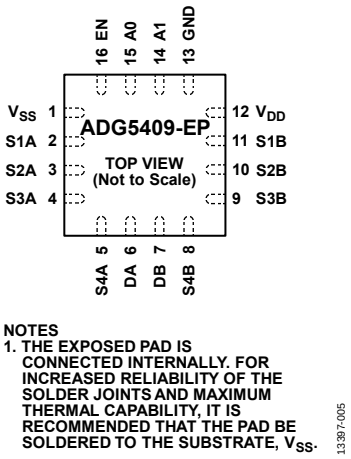

Figure 3. ADG5409-EP Pin Configuration

Table 10. ADG5409-EP Pin Function Descriptions

Pin No.	Mnemonic	Description
15	A0	Logic Control Input.
16	EN	Active High Digital Input. When low, the device is disabled and all switches are off. When high, Ax logic inputs determine on switches.
1	V_{SS}	Most Negative Power Supply Potential. In single-supply applications, this pin can be connected to ground.
2	S1A	Source Terminal 1A. This pin can be an input or an output.
3	S2A	Source Terminal 2A. This pin can be an input or an output.
4	S3A	Source Terminal 3A. This pin can be an input or an output.
5	S4A	Source Terminal 4A. This pin can be an input or an output.
6	DA	Drain Terminal A. This pin can be an input or an output.
7	DB	Drain Terminal B. This pin can be an input or an output.
8	S4B	Source Terminal 4B. This pin can be an input or an output.
9	S3B	Source Terminal 3B. This pin can be an input or an output.
10	S2B	Source Terminal 2B. This pin can be an input or an output.
11	S1B	Source Terminal 1B. This pin can be an input or an output.
12	V_{DD}	Most Positive Power Supply Potential.
13	GND	Ground (0 V) Reference.
14	A1	Logic Control Input.
EP	Exposed Pad	The exposed pad is connected internally. For increased reliability of the solder joints and maximum thermal capability, it is recommended that the pad be soldered to the substrate, V_{SS}.

Table 11. ADG5409-EP Truth Table

A1	A0	EN	On Switch Pair
X	X	0	None
0	0	1	1
0	1	1	2
1	0	1	3
1	1	1	4

TYPICAL PERFORMANCE CHARACTERISTICS

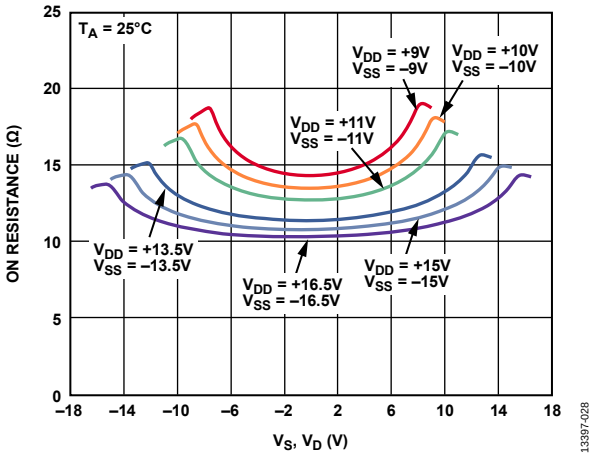

Figure 4. R_{ON} as a Function of V_S, V_D (Dual Supply)

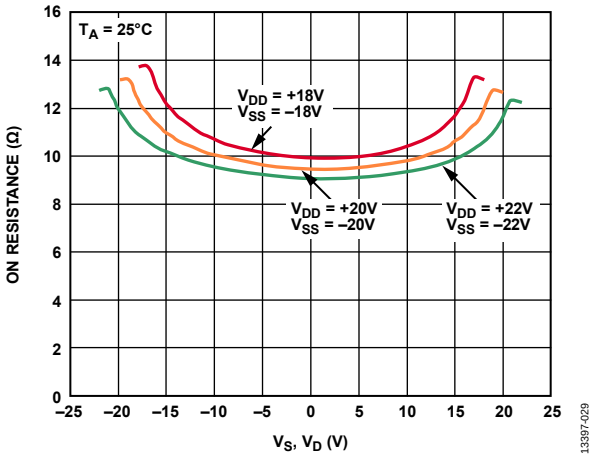

Figure 5. R_{ON} as a Function of V_S, V_D (Dual Supply)

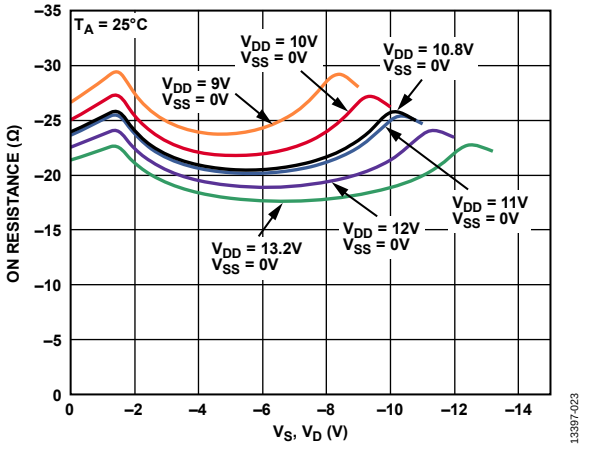

Figure 6. R_{ON} as a Function of V_S, V_D (Single Supply)

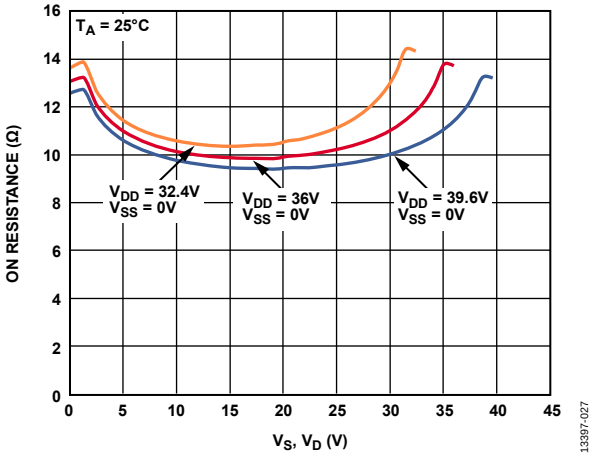

Figure 7. R_{ON} as a Function of V_S, V_D (Single Supply)

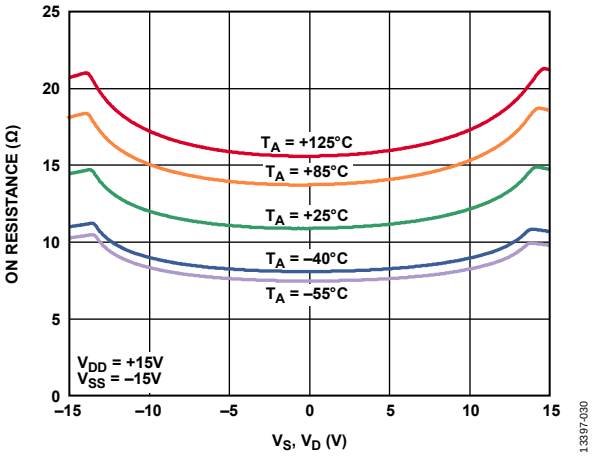

Figure 8. R_{ON} as a Function of V_S (V_D) for Different Temperatures, ±15 V Dual Supply

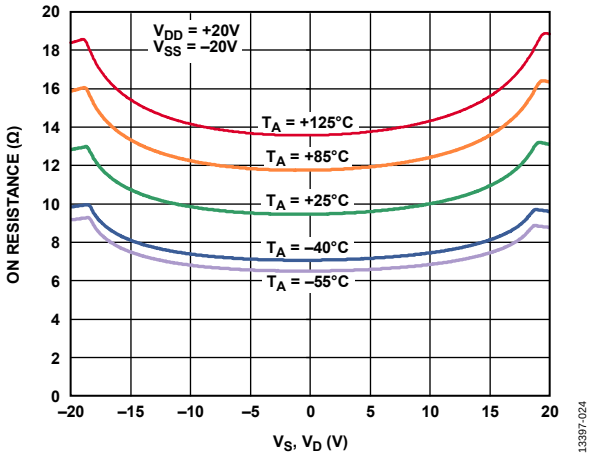

Figure 9. R_{ON} as a Function of V_S (V_D) for Different Temperatures, ±20 V Dual Supply

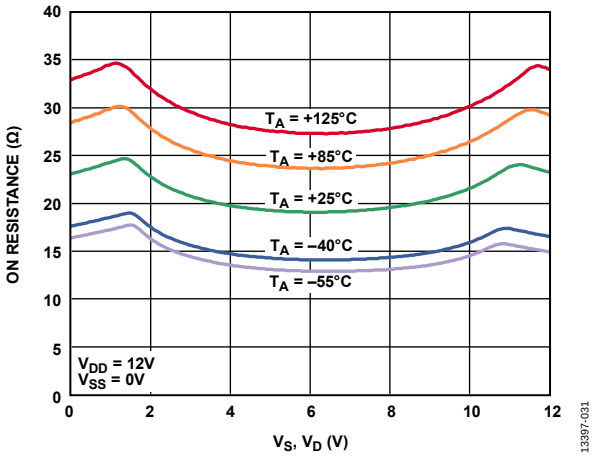

Figure 10. R_{ON} as a Function of V_S (V_D) for Different Temperatures, 12 V Single Supply

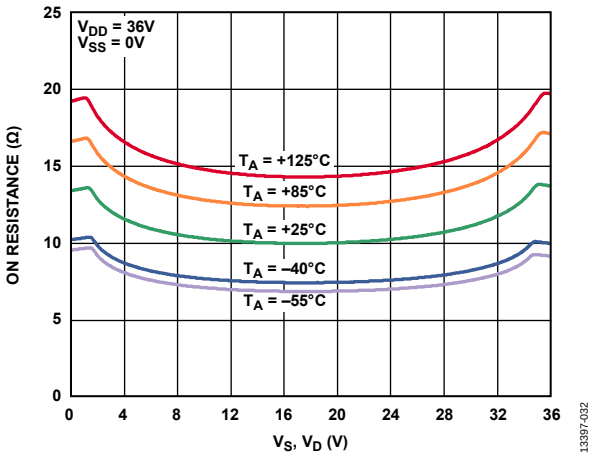

Figure 11. R_{ON} as a Function of V_D (V_S) for Different Temperatures, 36 V Single Supply

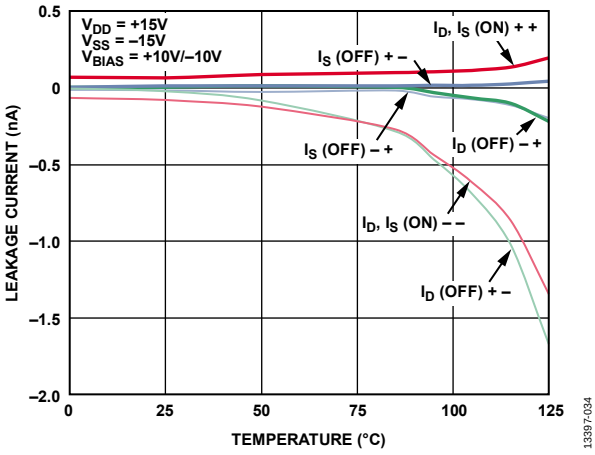

Figure 12. Leakage Currents vs. Temperature, ±15 V Dual Supply

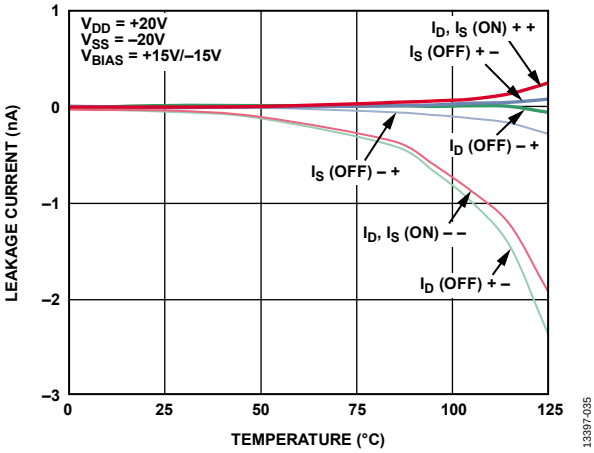

Figure 13. Leakage Currents vs. Temperature, ±20 V Dual Supply

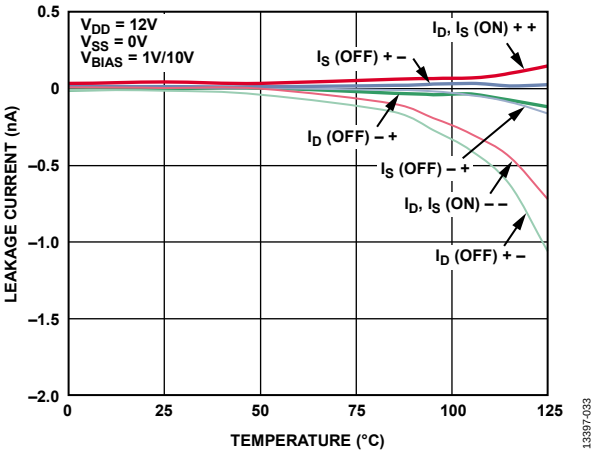

Figure 14. Leakage Currents vs. Temperature, 12 V Single Supply

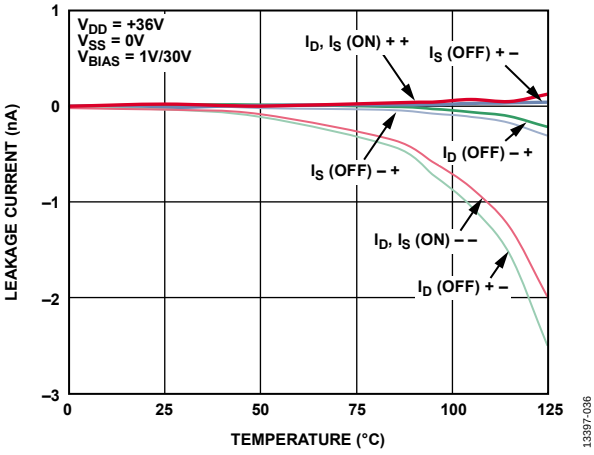

Figure 15. Leakage Currents vs. Temperature, 36 V Single Supply

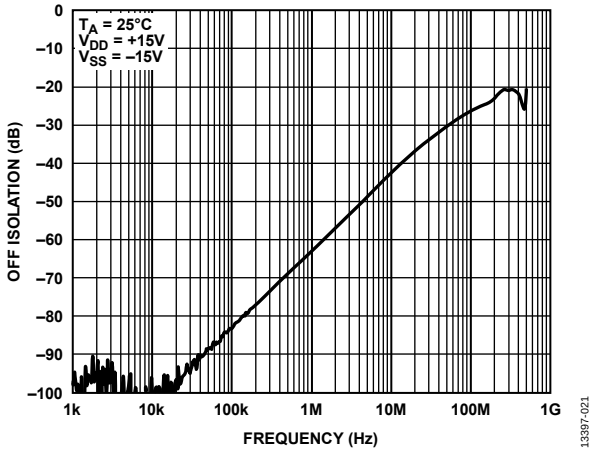

Figure 16. Off Isolation vs. Frequency, ±15 V Dual Supply

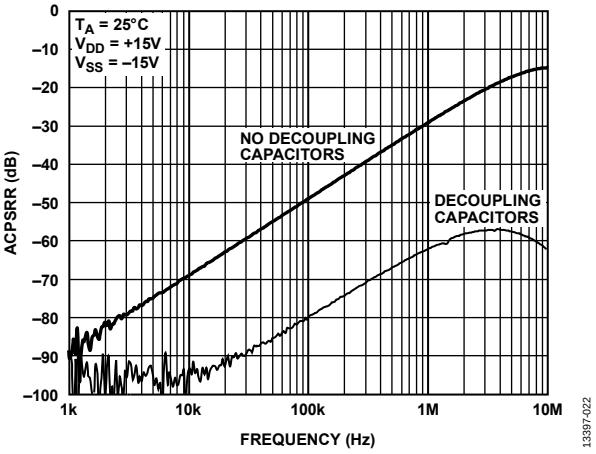

Figure 19. ACPSRR vs. Frequency, ±15 V Dual Supply

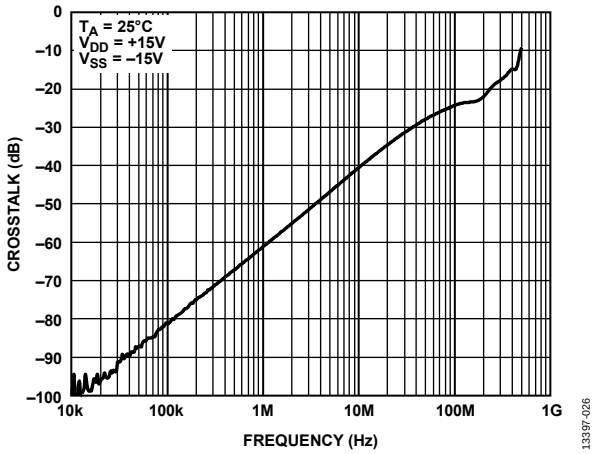

Figure 17. Crosstalk vs. Frequency, ±15 V Dual Supply

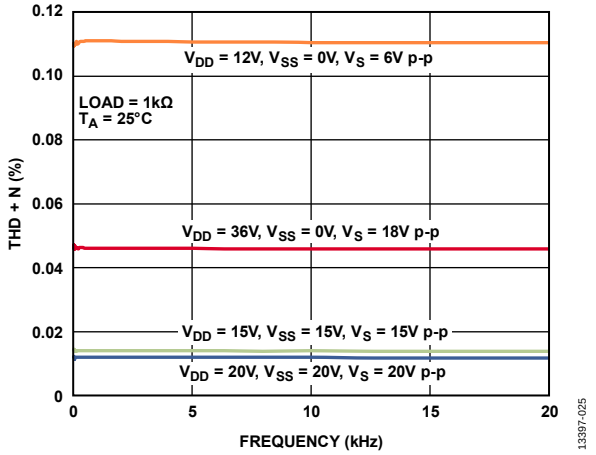

Figure 20. THD + N vs. Frequency

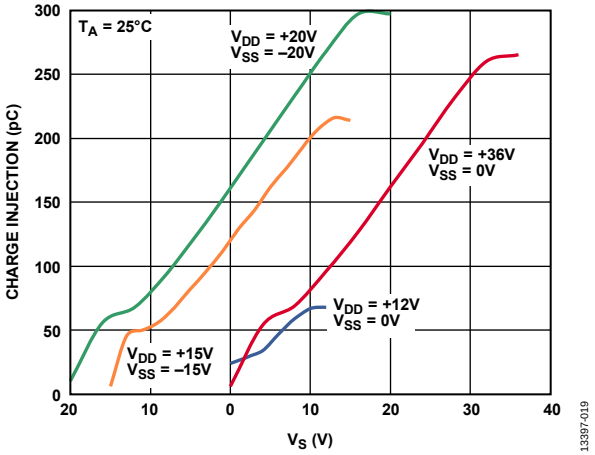

Figure 18. Charge Injection vs. Source Voltage

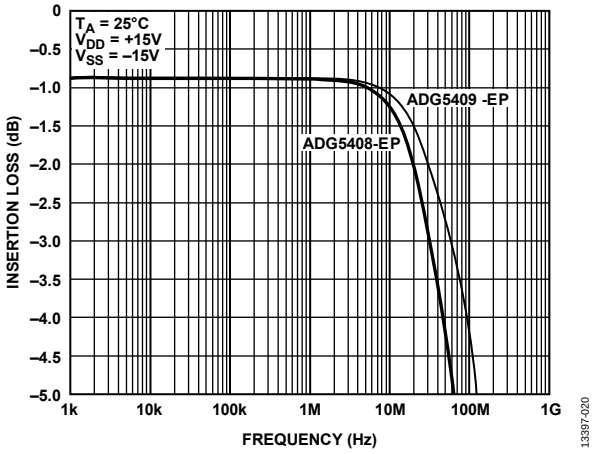

Figure 21. Bandwidth

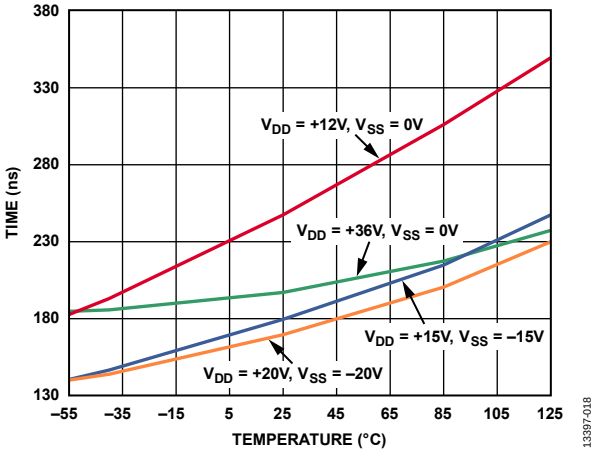

Figure 22. $t_{TRANSITION}$ Times vs. Temperature

TEST CIRCUITS

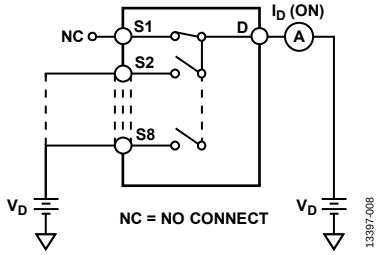

Figure 23. On Leakage

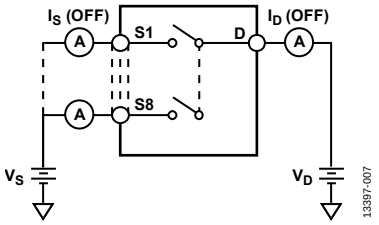

Figure 27. Off Leakage

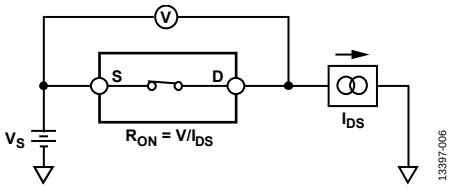

Figure 24. On Resistance

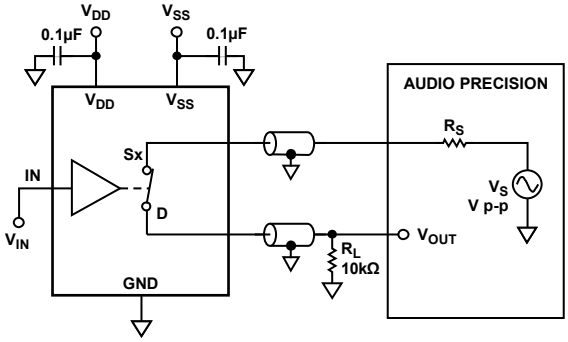

Figure 28. THD + Noise Figure

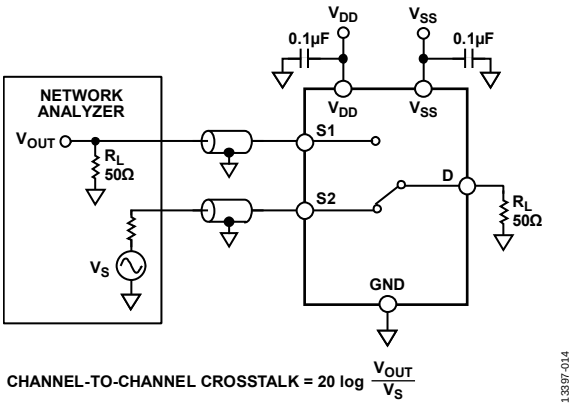

Figure 25. Channel-to-Channel Crosstalk

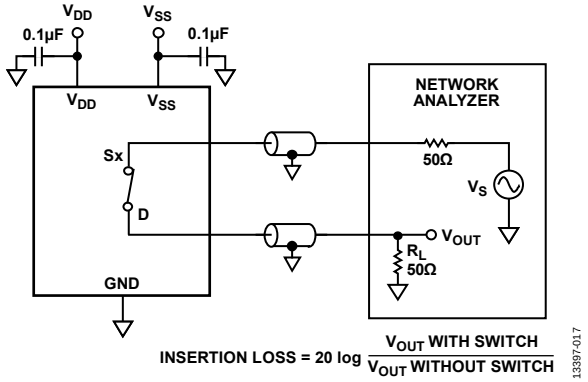

Figure 29. Bandwidth

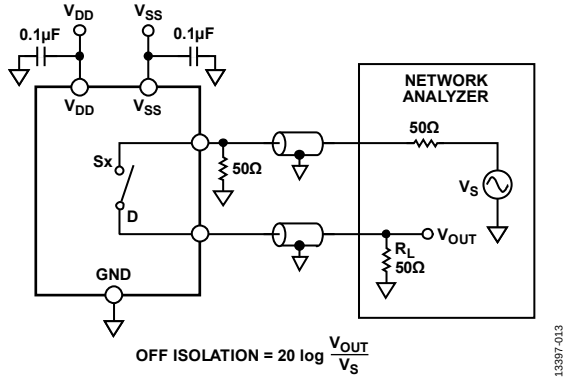

Figure 26. Off Isolation

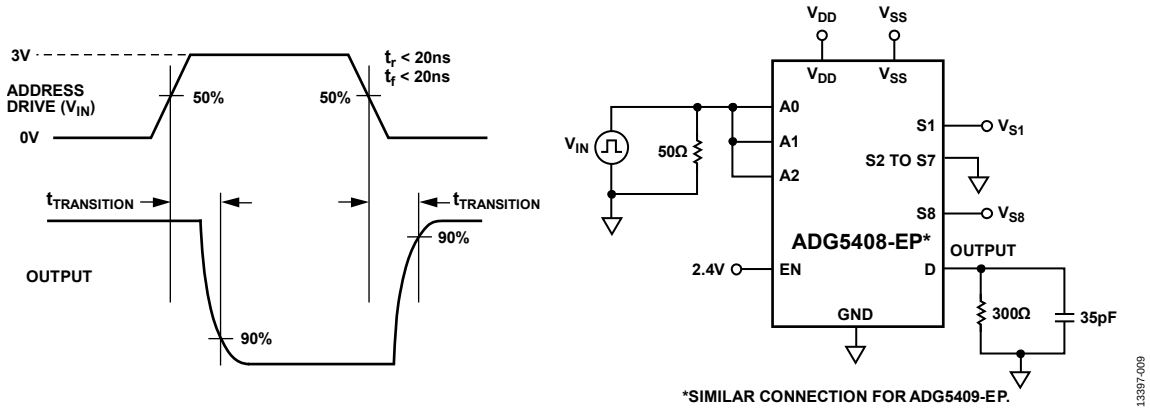

Figure 30. Address to Output Switching Times, $t_{TRANSITION}$

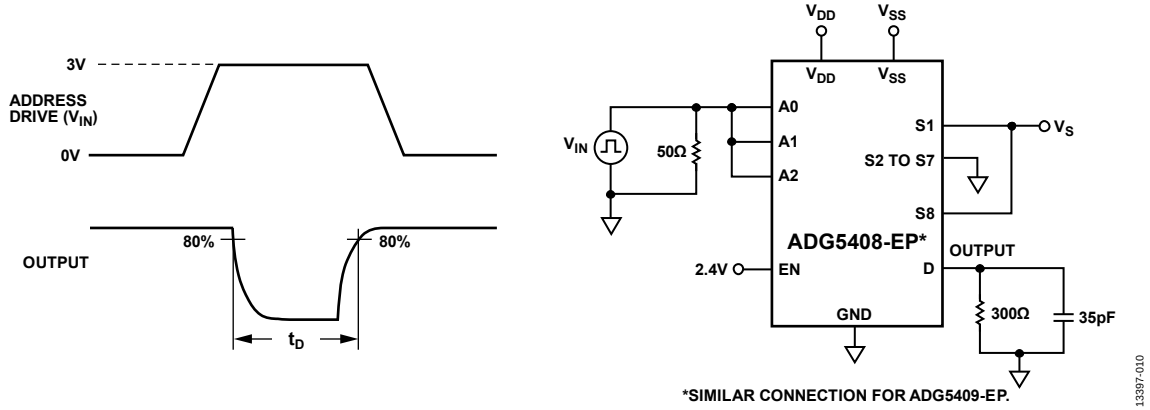

Figure 31. Break-Before-Make Delay, t_D

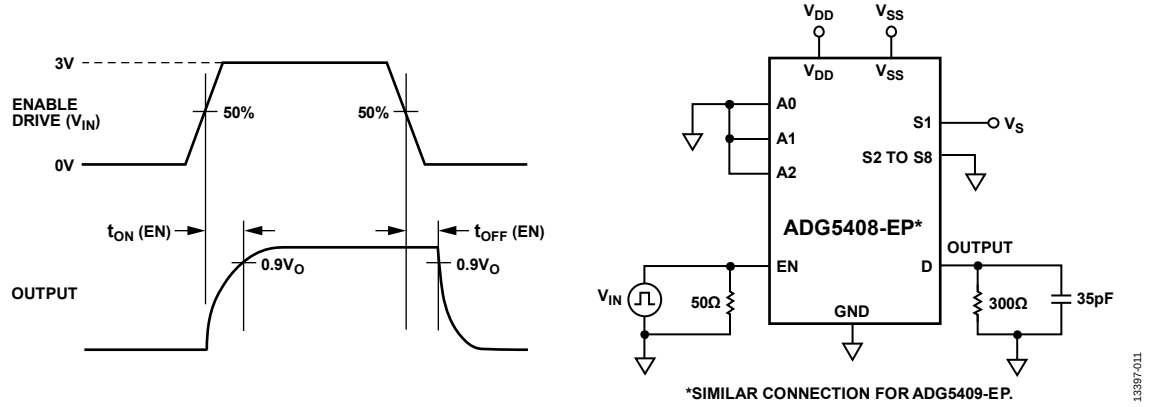

Figure 32. Enable Delay, t_{ON} (EN), t_{OFF} (EN)

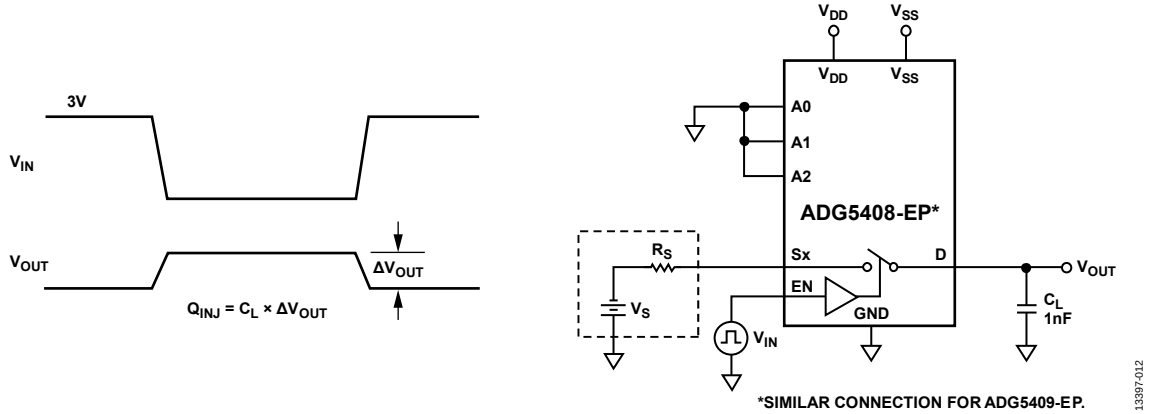

Figure 33. Charge Injection

OUTLINE DIMENSIONS

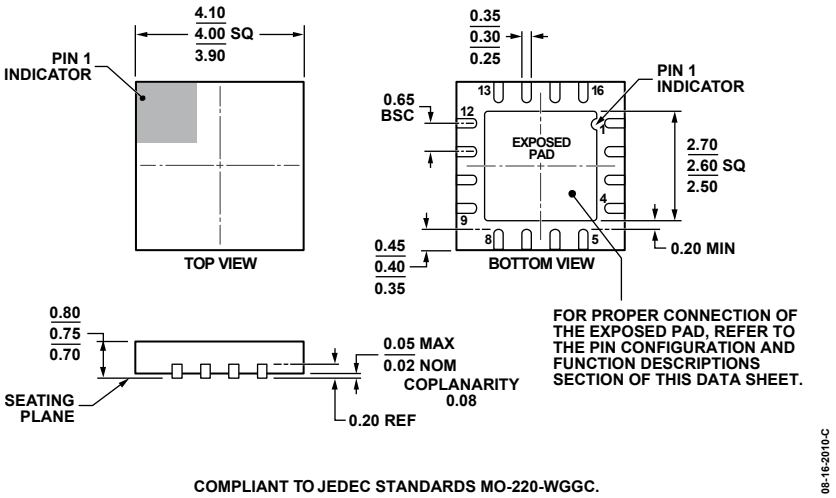

Figure 34. 16-Lead Lead Frame Chip Scale Package [LFCSP_WQ]
4 mm × 4 mm Body, Very Very Thin Quad
(CP-16-17)
Dimensions shown in millimeters

ORDERING GUIDE

Model[1]	Temperature Range	Package Description	Package Option
ADG5408TCPZ-EP-RL7	−55°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP_WQ]	CP-16-17
ADG5408TCPZ-EP	−55°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP_WQ]	CP-16-17
ADG5409TCPZ-EP-RL7	−55°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP_WQ]	CP-16-17
ADG5409TCPZ-EP	−55°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP_WQ]	CP-16-17

[1] Z = RoHS Compliant Part.